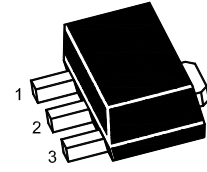


2SB1260U

PNP Silicon Epitaxial Planar Transistor

for power amplification applications



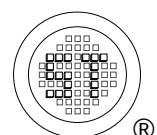
1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

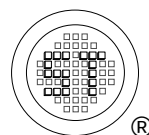
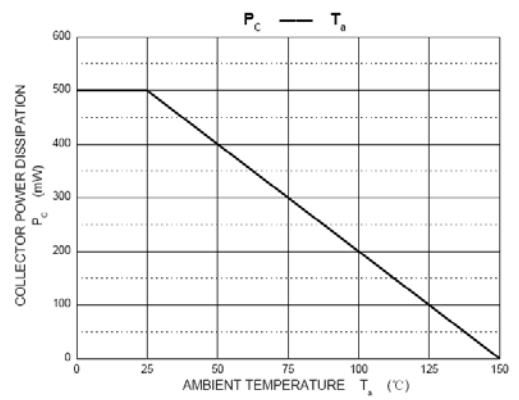
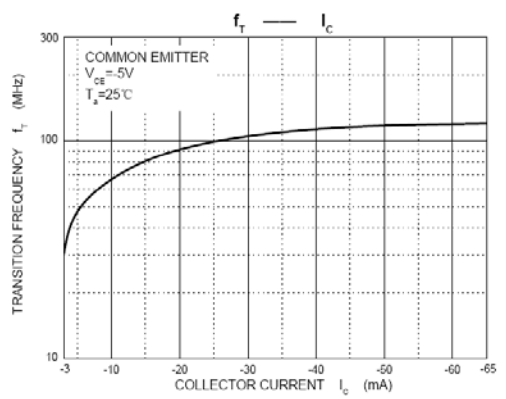
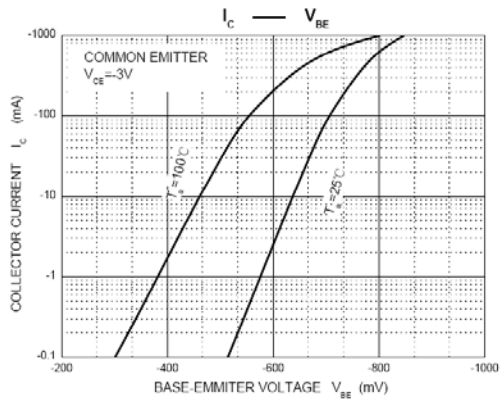
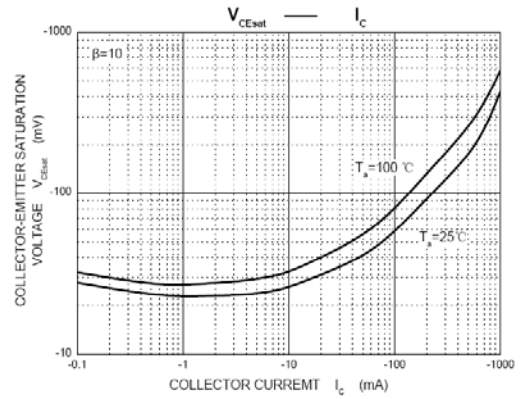
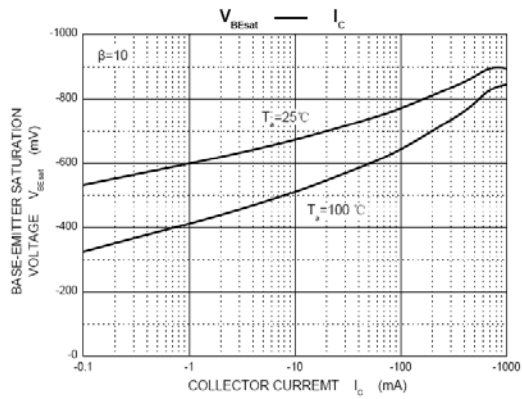
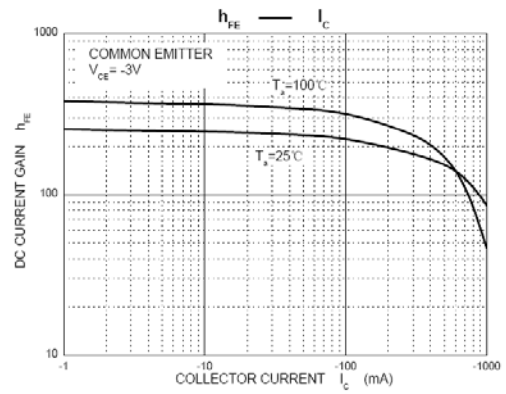
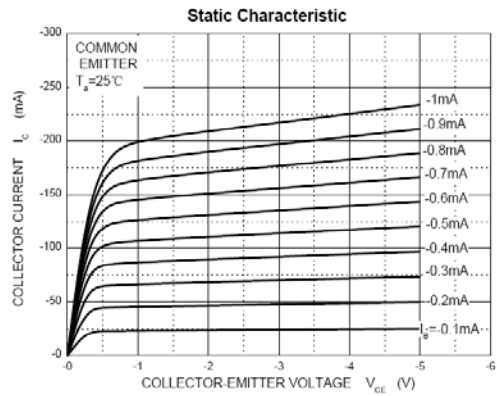
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	80	V
Collector Emitter Voltage	$-V_{CEO}$	80	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	1	A
Total Power Dissipation	P_{tot}	0.5	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

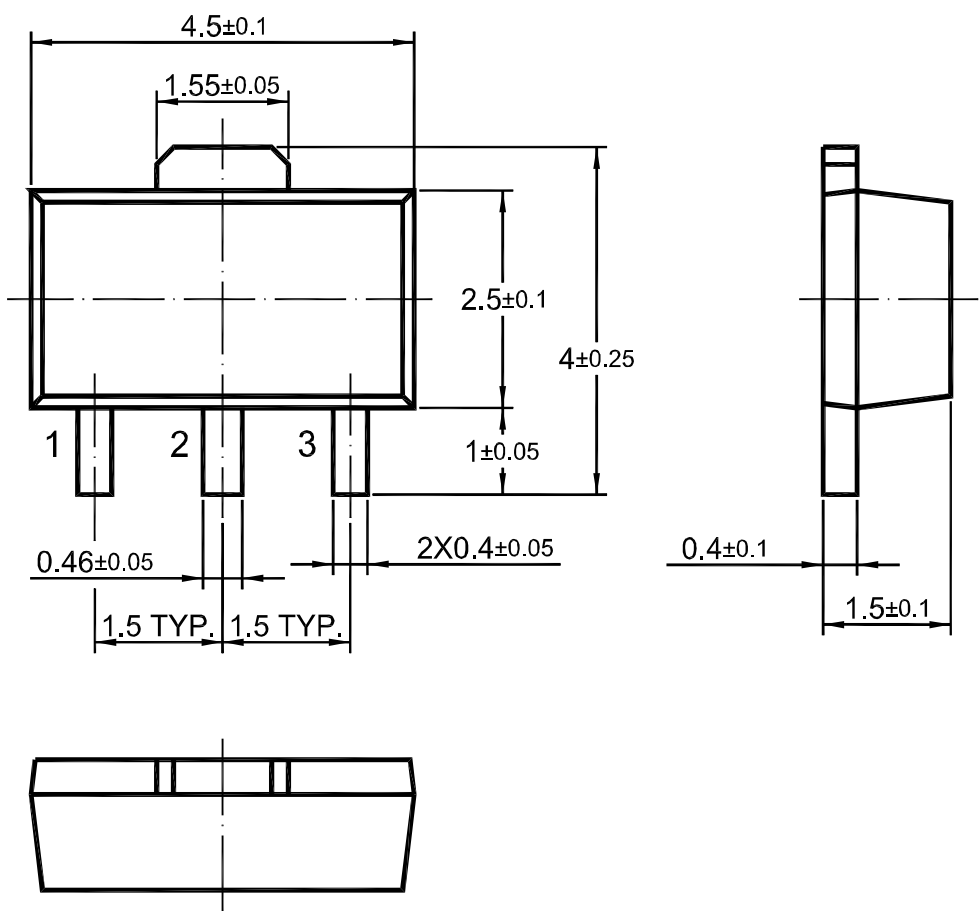
Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 3\text{ V}$, $-I_C = 100\text{ mA}$ Current Gain Group	P	h_{FE}	82	-	-
	Q	h_{FE}	120	-	-
	R	h_{FE}	180	-	-
Collector Base Cutoff Current at $-V_{CB} = 60\text{ V}$	$-I_{CBO}$	-	-	1	μA
Emitter Base Cutoff Current at $-V_{EB} = 4\text{ V}$	$-I_{EBO}$	-	-	1	μA
Collector Base Breakdown Voltage at $-I_C = 50\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	80	-		V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	80	-		V
Emitter Base Breakdown Voltage at $-I_E = 50\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-		V
Collector Emitter Saturation Voltage at $-I_C = 500\text{ mA}$, $-I_B = 50\text{ mA}$	$-V_{CE(sat)}$	-	-	0.4	V
Transition Frequency at $-V_{CE} = 5\text{ V}$, $-I_C = 50\text{ mA}$, $f = 30\text{ MHz}$	f_T	-	100	-	MHz
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	25	-	pF





2SB1260U

SOT-89 PACKAGE OUTLINE



Dimensions in mm

